United States Patent [19]

Bae

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[54] **PHOTORESIST FILM COATING METHOD**

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[52] **U.S. Cl.** **427/240**; 427/385.5; 437/231

[58] **Field of Search** 427/385.5, 240; 437/231

[56] **References Cited**

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[57] **ABSTRACT**

There is disclosed a method for the formation of photoresist film. The photoresist film of a semiconductor is formed by a method consisting broadly of: feeding a photoresist solution onto a rugged surface of a wafer which is rotated at a low speed, to form a photoresist film with a smooth surface; turning the wafer right over, to make the photoresist film of smooth surface look downward; and rotating the wafer at a high speed. The formed photoresist film becomes rugged along the topology of the wafer, resulting in close similarity in the thickness of the photoresist film. Owing to this similarity, the light absorptivity is almost identical all over the present photoresist film, so that advantages are effected such as an increase in the reliability and production yield of highly integrated semiconductor device.

3 Claims, 1 Drawing Sheet